

TEMPERATURE DEPENDENCE
OF THE CONCENTRATION
OF CARRIERS IN CdIn₂Te₄ CRYSTALS

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S u m m a r y

The temperature dependences of electric conduction, the Hall coefficient, thermoelectric power, and the dimensionless field of the transverse Nernst—Ettingshausen effect in CdIn₂Te₄ crystals have been investigated in the region of mixed conduction (250—420 K). Using the experimental data on these kinetic coefficients, we determined the concentrations and mobilities of electrons and holes and the Fermi level energy in the interval of temperatures 350—420 K, where the scattering of charge carriers by optic polarization vibrations of the crystal lattice is dominant.